

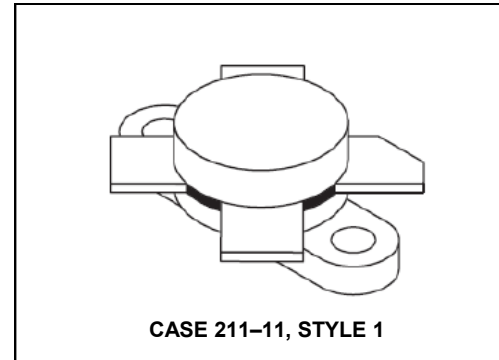
The RF Line NPN Silicon Power Transistor 150W(PEP), 30MHz, 50V

Rev. V1

Designed primarily for high-voltage applications as a high-power linear amplifier from 2.0 to 30 MHz. Ideal for marine and base station equipment.

- Specified 50 V, 30 MHz Characteristics —
 - Output power = 150 W (PEP)
 - Minimum gain = 13 DB
 - Efficiency = 45%
- Intermodulation distortion @ 150 W (PEP) —
 - IMD = -30 db (max.)
- 100% tested for load mismatch at all phase angles with 30:1 VSWR @ 150 W CW

Product Image



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	55	Vdc
Collector-Base Voltage	V_{CBO}	110	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	20	Adc
Withstand Current — 10 s	—	30	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	320 1.83	Watts W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.5	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 200\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	55	—	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 100\text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	110	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	110	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc

(continued)

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Rev. V1

ELECTRICAL CHARACTERISTICS — continued ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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ON CHARACTERISTICS

DC Current Gain ($I_C = 5.0\text{ Adc}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	10	30	—	—
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DYNAMIC CHARACTERISTICS

Output Capacitance ($V_{CB} = 50\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{OB}	—	220	250	pF
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FUNCTIONAL TESTS

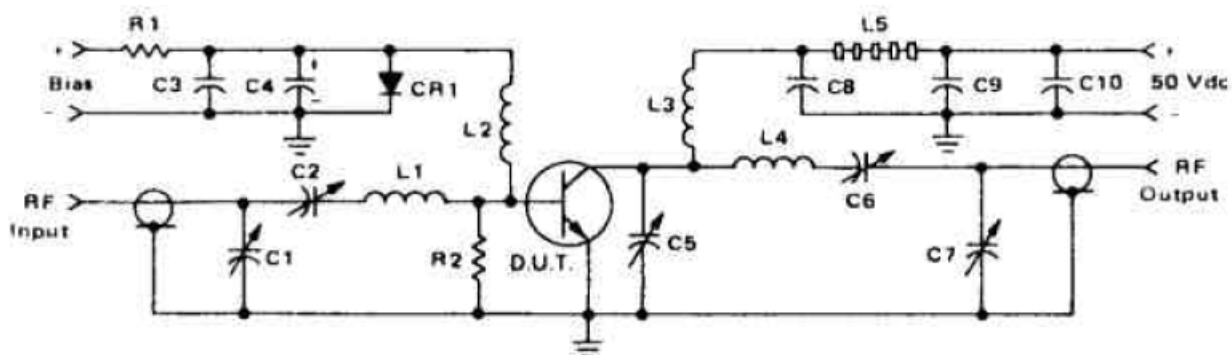
Common-Emitter Amplifier Gain ($V_{CC} = 50\text{ Vdc}$, $P_{OUT} = 150\text{ W (PEP)}$, $I_C(\text{max}) = 3.32\text{ Adc}$, $f = 30\text{ MHz}$)	G_{PE}	13	15	—	dB
Output Power ($V_{CE} = 50\text{ Vdc}$, $f = 30\text{ MHz}$)	P_{OUT}	150	—	—	W (PEP)
Collector Efficiency ($V_{CC} = 50\text{ Vdc}$, $P_{OUT} = 150\text{ W (PEP)}$, $I_C(\text{max}) = 3.32\text{ Adc}$, $f = 30\text{ MHz}$)	η	45	—	—	%
Intermodulation Distortion (1) ($V_{CE} = 50\text{ Vdc}$, $P_{OUT} = 150\text{ W (PEP)}$, $I_C = 3.32\text{ Adc}$)	IMD	—	-33	-30	dB
Electrical Ruggedness ($V_{CC} = 50\text{ Vdc}$, $P_{OUT} = 150\text{ W (PEP)}$, $I_C(\text{max}) = 3.32\text{ Adc}$, VSWR 30:1 at all Phase Angles)	Ψ	No Degradation in Output Power			

NOTE:

- To Mil-Std-1311 Version A, Test Method 2204B, Two Tone, Reference each Tone.

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Rev. V1



C1, C2, C7 — 170-780 pF, Arco 469
 C3, C8, C9 — 0.1 μ F, 100 V Erie
 C4 — 500 μ F @ 6.0 V
 C5 — 9.0-180 pF, Arco 463
 C6 — 80-480 pF, Arco 466
 C10 — 30 μ F, 100 V
 R1 — 10 Ω , 10 Watt

R2 — 10 Ω , 1.0 Watt
 CR1 — 1N4997
 L1 — 3 Turns, #16 Wire, 5/16" I.D., 5/16" Long
 L2 — 10 μ H Molded Choke
 L3 — 12 Turns, #16 Enameled Wire Closewound, 1/4" I.D.
 L4 — 5 Turns, 1/8" Copper Tubing, 9/16" I.D., 3/4" Long
 L5 — 10 Ferrite Beads — Ferroxcube #56-590-65/3B

Figure 1. 30 MHz Test Circuit Schematic

FIGURE 2 — OUTPUT POWER versus INPUT POWER

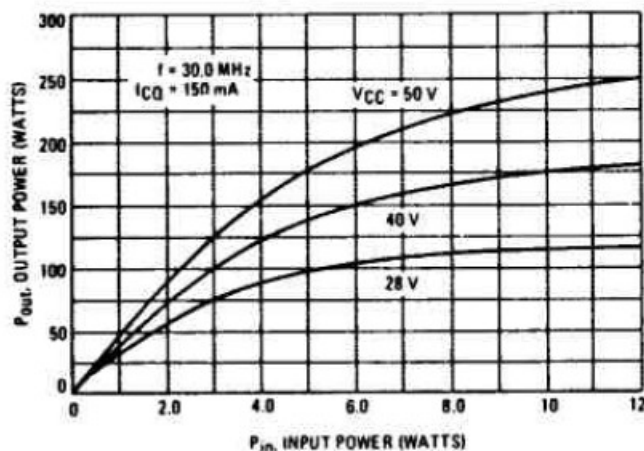
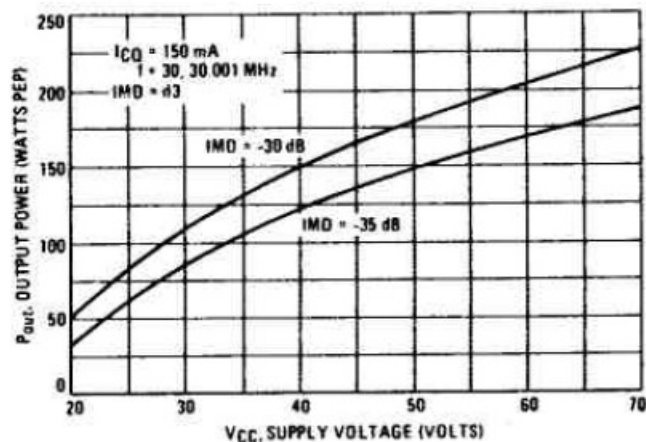


FIGURE 3 — OUTPUT POWER versus SUPPLY VOLTAGE



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Rev. V1

FIGURE 4 – POWER GAIN versus FREQUENCY

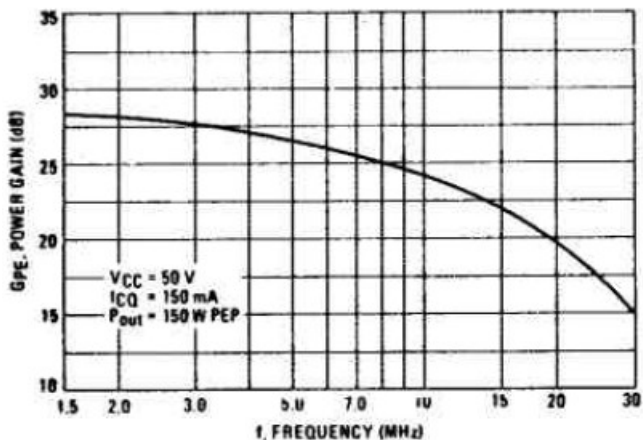
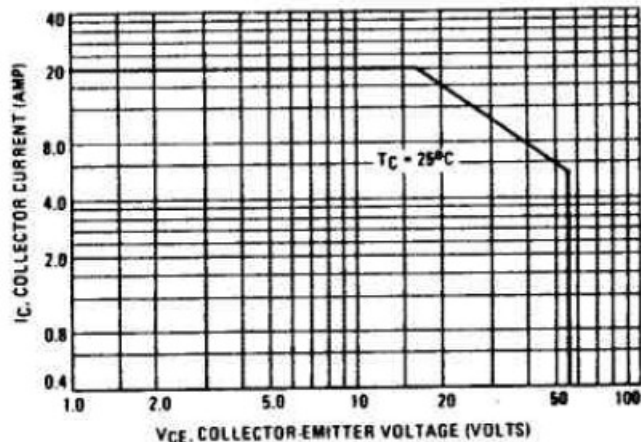


FIGURE 5 – DC SAFE OPERATING AREA



INTERMODULATION DISTORTION versus OUTPUT POWER

FIGURE 6 – V_{CC} = 40 Vdc

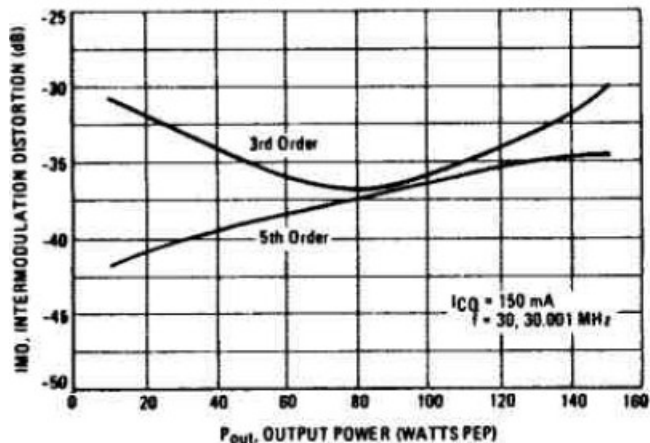
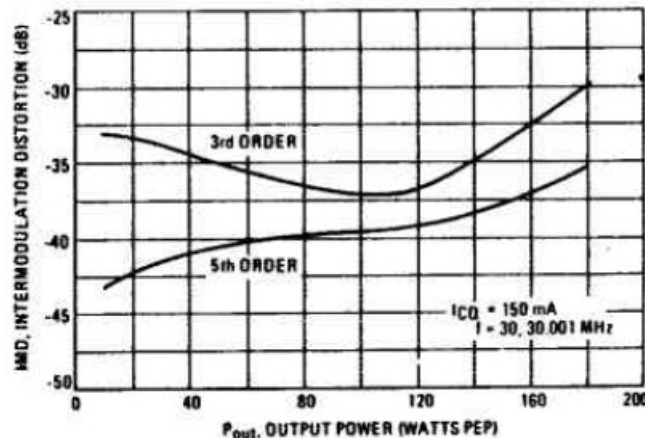


FIGURE 7 – V_{CC} = 50 Vdc



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Rev. V1

FIGURE 8 – OUTPUT CAPACITANCE versus FREQUENCY

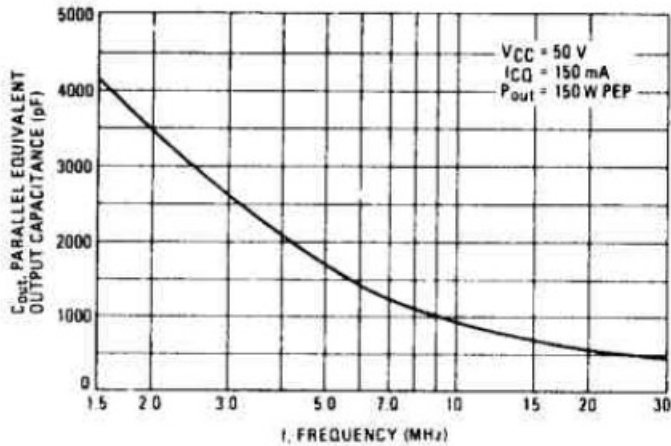
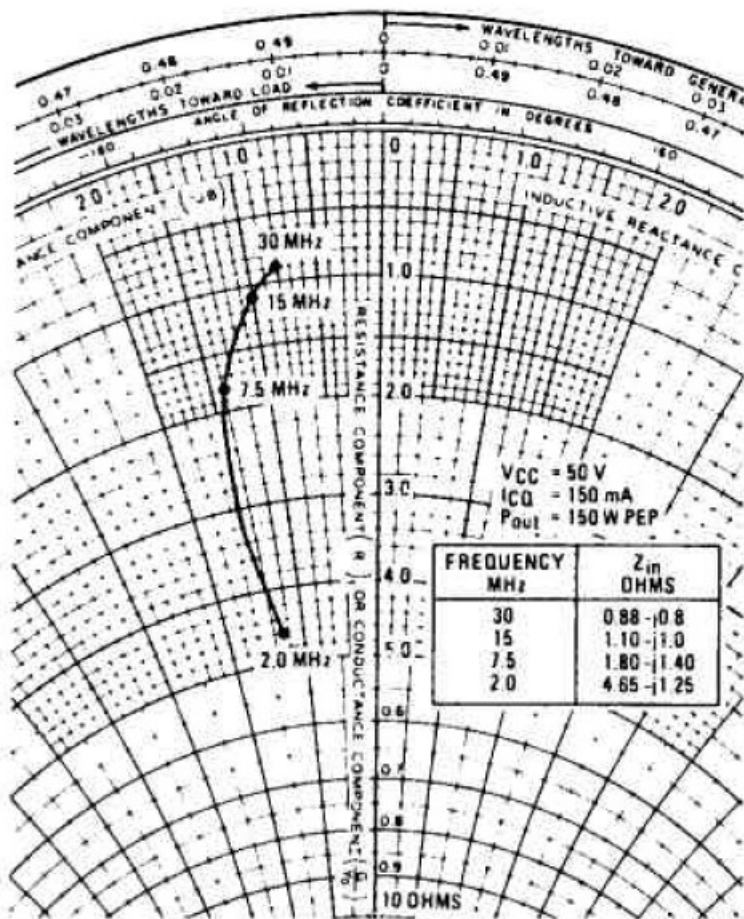
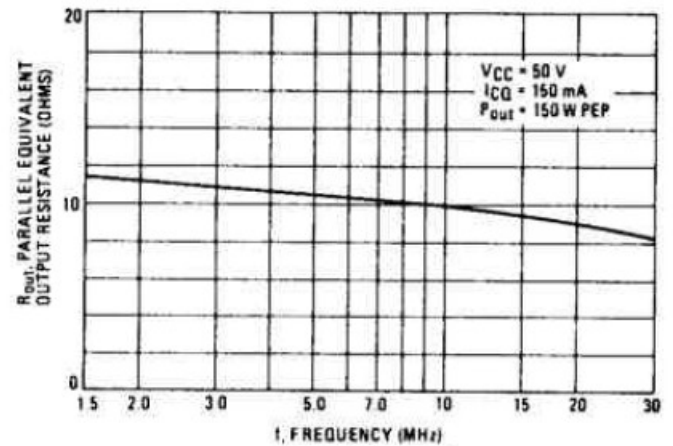
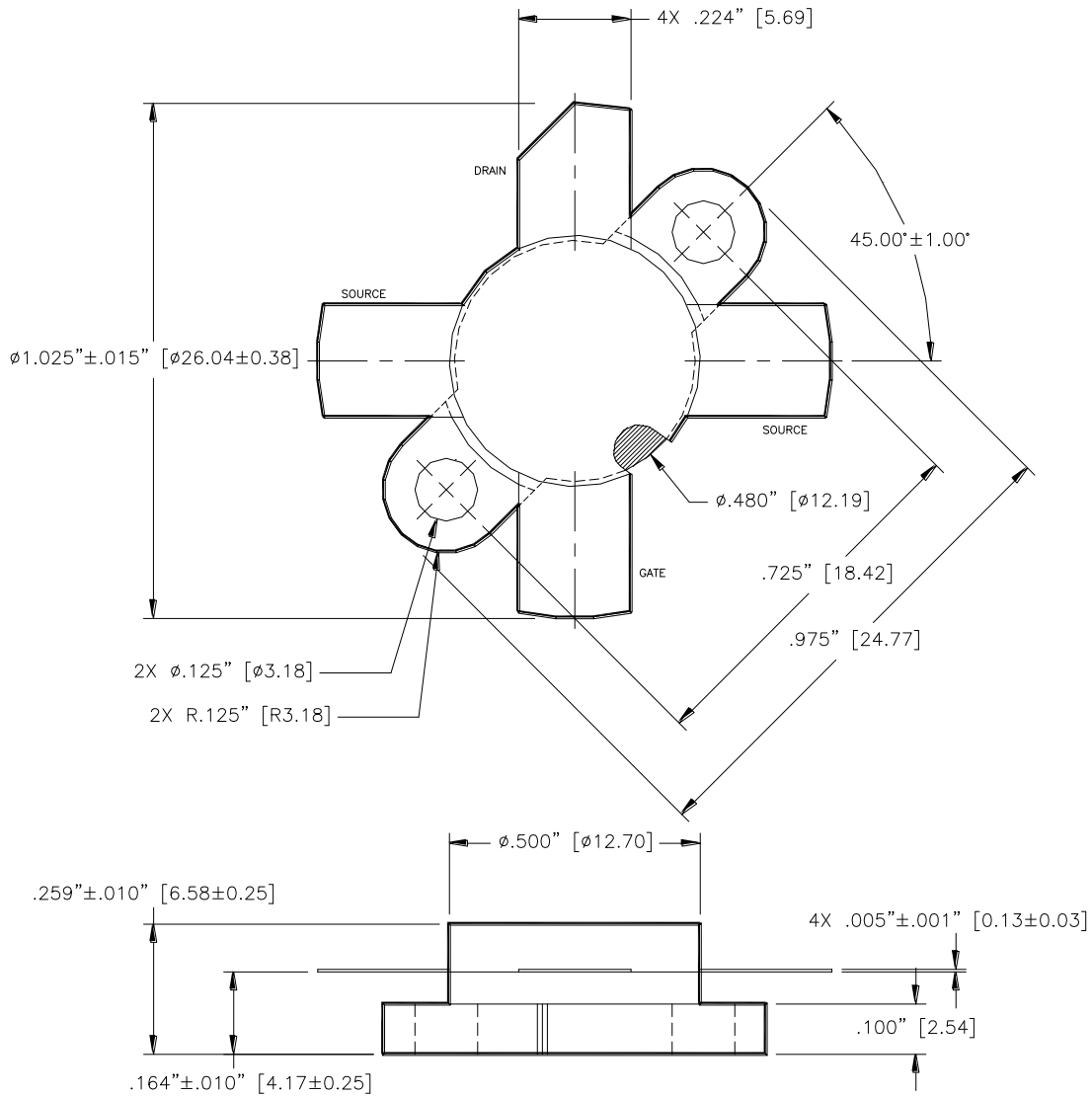


FIGURE 9 – OUTPUT RESISTANCE versus FREQUENCY



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Rev. V1



Unless otherwise noted, tolerances are inches $\pm .005''$ [millimeters $\pm 0.13\text{mm}$]